

What is claimed is:

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- 5 1. A method of wiring formation comprising the steps of:
forming a feeder film partially on a substrate;
forming on the substrate a plating base film such that
the plating base film partially overlaps the feeder film;
forming a plated wiring on the plating base film; and
selectively removing at least a portion of the feeder
film that is exposed from the plated wiring.
- 10 2. A method of wiring formation according to Claim 1,
wherein the step of forming on the substrate a plating base
film is performed using a physical film making process.
- 15 3. A method of wiring formation according to Claim 1,
wherein the step of forming a plated wiring on the plating base
film is performed using an electrolytic plating process.
- 20 4. A method of wiring formation according to Claim 1,
wherein the step of selectively removing at least a portion of
the feeder film that is exposed from the plated wiring is
performed using a wet etching process.
- 25 5. A method of wiring formation according to Claim 1,
wherein a width of a portion of the plating base film that is
stacked on the feeder film is wider than the smallest wire
width of the feeder film.
- 30 6. A method of wiring formation according to Claim 1,
wherein the plating base film comprises at least one of an
adhesive layer and a diffusion preventive layer.

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7. A method of wiring formation comprising the steps of:
forming a feeder film partially on a substrate;
forming on the substrate a resist pattern which has an
opening defining a wiring forming area, such that a portion of
the feeder film is exposed from the opening in the resist
pattern;
forming a plating base film at least on the substrate in
the opening;
forming a plated wiring on the plating base film in the
opening;
removing the resist pattern; and
selectively removing at least a portion of the feeder
film that is exposed from the plated wiring.
8. A method of wiring formation according to Claim 7,
wherein the step of forming on the substrate a plating base
film is performed using a physical film making process.
9. A method of wiring formation according to Claim 7,
wherein the step of forming a plated wiring on the plating base
film is performed using an electrolytic plating process.
10. A method of wiring formation according to Claim 7,
wherein the step of selectively removing at least a portion of
the feeder film that is exposed from the plated wiring is
performed using a wet etching process.
11. A method of wiring formation according to Claim 7,
wherein a width of a portion of the plating base film that is
stacked on the feeder film is wider than the smallest wire
width of the feeder film.

12. A method of wiring formation according to Claim 7, wherein the plating base film comprises at least one of an adhesive layer and a diffusion preventive layer.

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13. A method of manufacturing an electronic component comprising the steps of:

providing a substrate;

forming a feeder film partially on the substrate;

10 forming on the substrate a plating base film by using a physical film making process such that the plating base film partially overlaps the feeder film;

forming a plated wiring on the plating base film using an electrolytic plating process; and

15 selectively removing at least a portion of the feeder film that is exposed from the plated wiring, using a wet etching process.

14. A method according to Claim 13, wherein a width of a portion of the plating base film that is stacked on the feeder film is wider than the smallest wire width of the feeder film.

15. A method according to Claim 13, wherein a width of a portion of the plating base film that is stacked on the feeder film is wider than the smallest wire width of the feeder film.

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16. A method according to Claim 13, wherein the plating base film comprises at least one of an adhesive layer and a diffusion preventive layer.

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17. A method of manufacturing an electronic component comprising the steps of:

providing a substrate;

forming a feeder film partially on a substrate;

5 forming on the substrate a resist pattern which has an opening defining a wiring forming area, such that a portion of the feeder film is exposed from the opening in the resist pattern;

forming a plating base film at least on the substrate in the opening using a physical film making process;

forming a plated wiring on the plating base film in the opening using an electrolytic plating process;

removing the resist pattern; and

15 selectively removing at least a portion of the feeder film that is exposed from the plated wiring, using a wet etching.

18. A method according to Claim 17, wherein a width of a portion of the plating base film that is stacked on the feeder film is wider than the smallest wire width of the feeder film.

19. A method according to Claim 17, wherein a width of a portion of the plating base film that is stacked on the feeder film is wider than the smallest wire width of the feeder film.

20. A method according to Claim 17, wherein the plating base film comprises at least one of an adhesive layer and a diffusion preventive layer.